

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.



Dual Common Drain P-Channel PowerTrench[®] MOSFET -20 V, -7 A, 36 m Ω

Features

- Max $r_{S1S2(on)}$ = 36 m Ω at V_{GS} = -4.5 V, I_D = -5.7 A
- Max $r_{S1S2(on)}$ = 50 m Ω at V_{GS} = -2.5 V, I_D = -4.6 A
- Low Profile 0.8 mm maximum in the new package MicroFET 2x3 mm
- HBM ESD protection level 2.8 kV (Note 3)
- RoHS Compliant

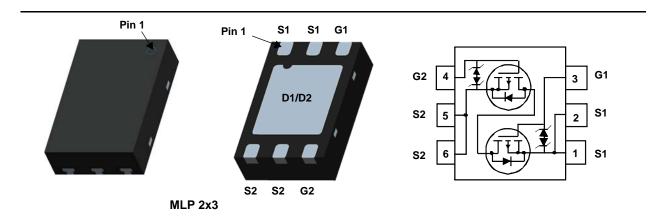


General Description

This device is designed specifically as a single package solution for Li-Ion battery pack protection circuit and other ultra-portable applications. It features two common drain P-channel MOSFETs, which enables bidirectional current flow, on Fairchild's advanced PowerTrench[®] process with state of the art MircoFET Leadframe, the FDMB2308PZ minimizes both PCB space and $r_{S1S2(on)}$.

Application

Li-Ion Battery Pack



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{S1S2}	Source1 to Source2 Voltage			-20	V
V _{GS}	Gate to Source Voltage			±12	V
	Source1 to Source2 Current -Continuous	T _A = 25 °C	(Note 1a)	-7	^
IS1S2	-Pulsed			-30	Α
P _D	Power Dissipation	T _A = 25 °C	(Note 1a)	2.2	W
	Power Dissipation	T _A = 25 °C	(Note 1b)	0.8	vv
T _J , T _{STG}	Operating and Storage Junction Temperature I	Range		-55 to +150	°C

Thermal Characteristics

R_{\thetaJA}	Thermal Resistance, Junction to Ambient	(Note 1a)	57	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	161	0/11

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
308	FDMB2308PZ	MLP 2x3	7"	8 mm	3000 units

FDMB2308PZ Dual Common Drain P-Channel PowerTrench® MOSFET
nmon Draii
n P-Chann
el PowerTr
ench [®] M
OSFET

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Chara	acteristics						
I _{S1S2}	Zero Gate Voltage Source1 to Source2 Current	$V_{S1S2} = -16 V, V_{GS} = 0 V$			-1	μΑ	
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12 \text{ V}, V_{S1S2} = 0 \text{ V}$			±10	μA	
On Chara	octeristics						
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{S1S2}, I_{S1S2} = -250 \ \mu A$	-0.6	-0.9	-1.5	V	
r _{S1S2(on)}		$V_{GS} = -4.5 \text{ V}, \ I_{S1S2} = -5.7 \text{ A}$		27	36	1	
	Statia Source1 to Source2 On Resistance	V _{GS} = -2.5 V, I _{S1S2} = -4.6 A		36	50		
	Static Source1 to Source2 On Resistance	$V_{GS} = -4.5 \text{ V}, \ I_{S1S2} = -5.7 \text{ A},$ $T_J = 125 \ ^{\circ}\text{C}$		35	49	- mΩ	
9fs	Forward Transconductance	V _{S1S2} = -5 V, I _{S1S2} = -5.7 A		29		S	
Dynamic	Characteristics						
C _{iss}	Input Capacitance			2280	3030	pF	
C _{oss}	Output Capacitance	V _{S1S2} = -10 V, V _{GS} = 0 V, f = 1 MHz		361	540	pF	
C _{rss}	Reverse Transfer Capacitance			339	510	pF	
Switching	g Characteristics						
t _{d(on)}	Turn-On Delay Time			14	25	ns	
t _r	Rise Time	V_{S1S2} = -10 V, I_{S1S2} = -5.7 A V _{GS} = -4.5 V, R _{GEN} = 6 Ω		33	52	ns	
t _{d(off)}	Turn-Off Delay Time			74	118	ns	
t _f	Fall Time			58	93	ns	
Q _g	Total Gate Charge	V _{S1S2} = -10 V, I _{S1S2} = -5.7 A,		22	30	nC	
Q _{gs}	Gate1 to Source1 Charge	$V_{G1S1} = -4.5 V, V_{G2S2} = 0 V$		3.6		nC	
Q _{gd}	Gate1 to Source2 "Miller" Charge			7.7		nC	
Source1-	Source2 Diode Characteristics						
I _{fss}	Maximum Continuous Source1-Source2 Diode Forward Current				-5.7	А	
V _{fss}	Source1 to Source2 Diode Forward Voltage	$V_{G1S 1} = 0 V, V_{G2S2} = -4.5 V,$ $I_{fss} = -5.7 A$ (Note 2)		-1	-1.6	V	



a. 57 °C/W when mounted on a 1 in² pad of 2 oz copper

000

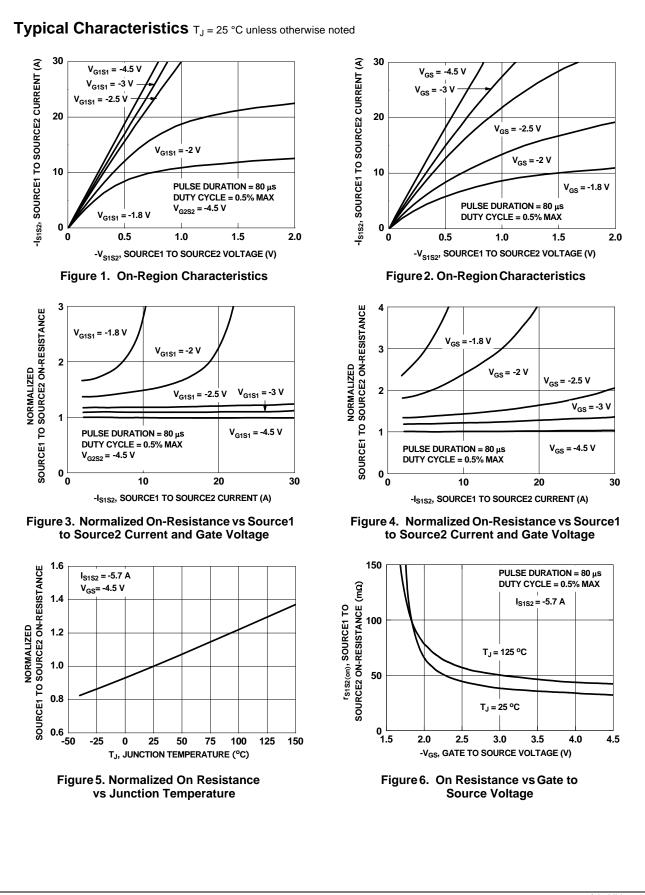
00000

b. 161 °C/W when mounted on

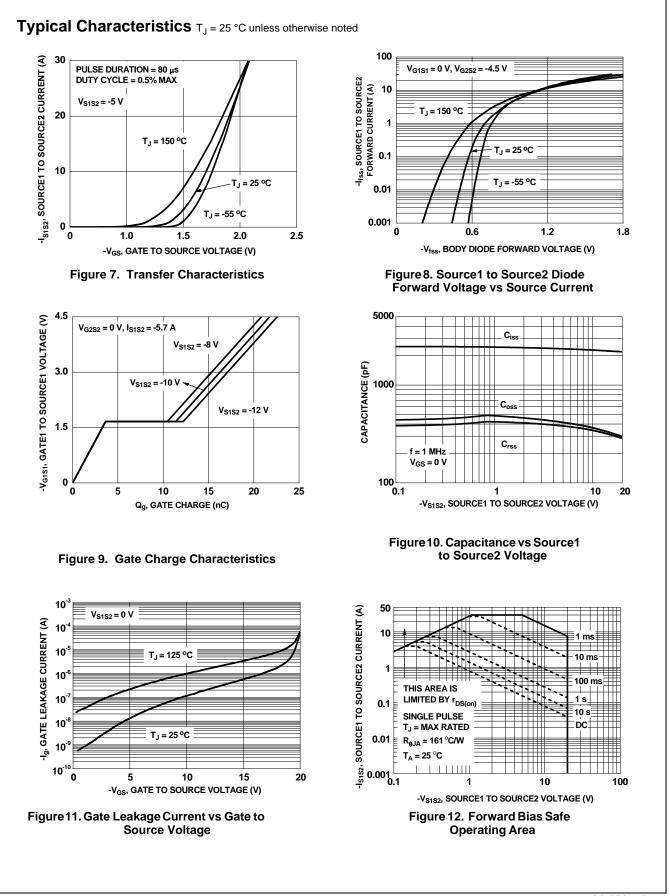
a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 $\mu s,$ Duty cycle < 2.0%.

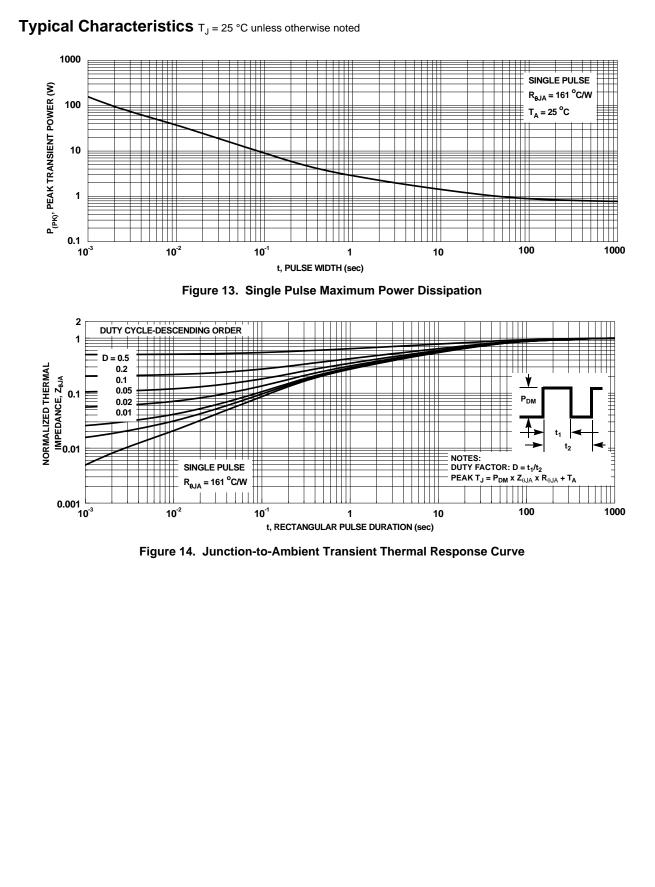
3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.



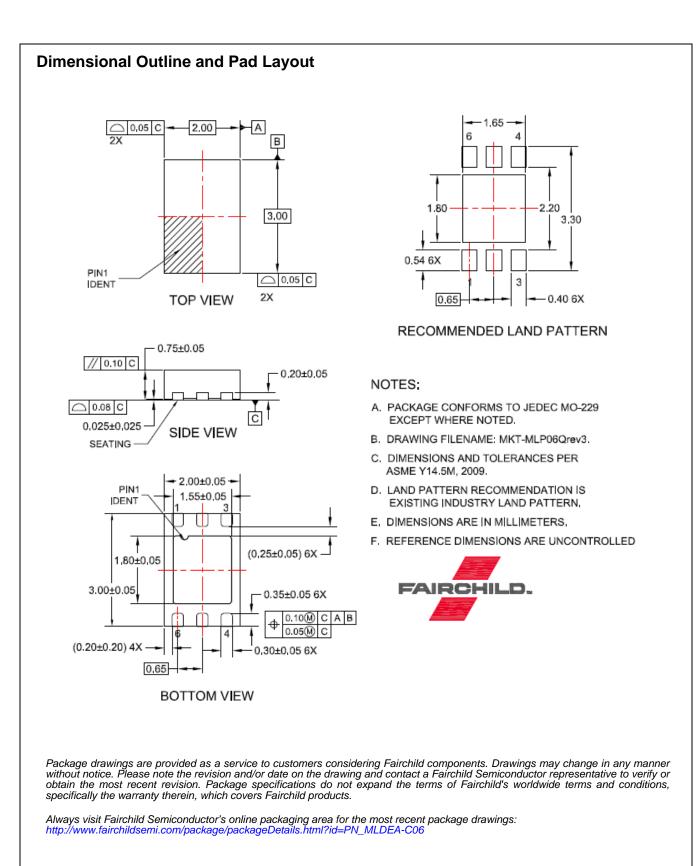
©2013 Fairchild Semiconductor Corporation FDMB2308PZ Rev.C3



©2013 Fairchild Semiconductor Corporation FDMB2308PZ Rev.C3 FDMB2308PZ Dual Common Drain P-Channel PowerTrench[®] MOSFET



FDMB2308PZ Rev.C3



©2013 Fairchild Semiconductor Corporation FDMB2308PZ Rev.C3



DMB2308PZ Dual Common Drain P-Channel PowerTrench[®] MOSFET

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi: FDMB2308PZ